

IGBT

GD100FFT120C6S

Molding Type Module

1200V/100A 6 in one-package



Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Description	GD100FFT120C6S	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 30	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=80^{\circ}\text{C}$	180 100	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	200	A
I_F	Diode Continuous Forward Current @ $T_C=80^{\circ}\text{C}$	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	579	W
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V
Mounting Torque	Mounting Screw:M5	3.0 to 6.0	N.m

Electrical Characteristics of IGBT $T_C=25^{\circ}\text{C}$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$T_j=25^{\circ}\text{C}$	1200			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}$, $V_{GE}=0\text{V}$, $T_j=25^{\circ}\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}$, $V_{CE}=0\text{V}$, $T_j=25^{\circ}\text{C}$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=5.0\text{mA}$, $V_{CE}=V_{GE}$, $T_j=25^{\circ}\text{C}$	5.0	5.7	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}$, $V_{GE}=15\text{V}$, $T_j=25^{\circ}\text{C}$		1.90	2.35	V
		$I_C=100\text{A}$, $V_{GE}=15\text{V}$, $T_j=175^{\circ}\text{C}$		2.50		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=100A,$ $R_G=5.1\Omega, V_{GE}=\pm 15V,$ $T_j=25^\circ C$		257		ns
t_r	Rise Time			54		ns
$t_{d(off)}$	Turn-Off Delay Time			261		ns
t_f	Fall Time			176		ns
E_{on}	Turn-On Switching Loss			2.60		mJ
E_{off}	Turn-Off Switching Loss			3.67		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=100A,$ $R_G=5.1\Omega, V_{GE}=\pm 15V,$ $T_j=125^\circ C$		327		ns
t_r	Rise Time			62		ns
$t_{d(off)}$	Turn-Off Delay Time			326		ns
t_f	Fall Time			175		ns
E_{on}	Turn-On Switching Loss			5.45		mJ
E_{off}	Turn-Off Switching Loss			7.69		mJ
C_{ies}	Input Capacitance	$V_{CE}=30V, f=1MHz,$ $V_{GE}=0V$		12.8		nF
C_{oes}	Output Capacitance			0.46		nF
C_{res}	Reverse Transfer Capacitance			0.32		nF
Q_G	Gate Charge	$V_{CC}=600V, I_C=100A,$ $V_{GE}=0-15V$		605		nC
I_{SC}	SC Data	$t_p \leq 10\mu s, V_{GE}=15V,$ $T_j=125^\circ C, V_{CC}=900V,$ $V_{CEM} \leq 1200V$		890		A
L_{CE}	Stray Inductance			21		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal To Chip			1.80		m Ω

Electrical Characteristics of Diode $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _F	Diode Forward Voltage	I _F =100A	T _j =25°C		1.80	2.20	V
			T _j =125°C		1.85		
Q _r	Recovered Charge	I _F =100A, V _R =600V, R _G =5.1Ω, V _{GE} =-15V	T _j =25°C		8.3		μC
			T _j =125°C		11.8		
I _{RM}	Peak Reverse Recovery Current		T _j =25°C		116		A
			T _j =125°C		136		
E _{rec}	Reverse Recovery Energy		T _j =25°C		3.98		mJ
			T _j =125°C		7.93		

Electrical Characteristics of NTC $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per IGBT)		0.259	K/W
$R_{\theta JC}$	Junction-to-Case (per Diode)		0.384	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.009		K/W
Weight	Weight of Module	300		g

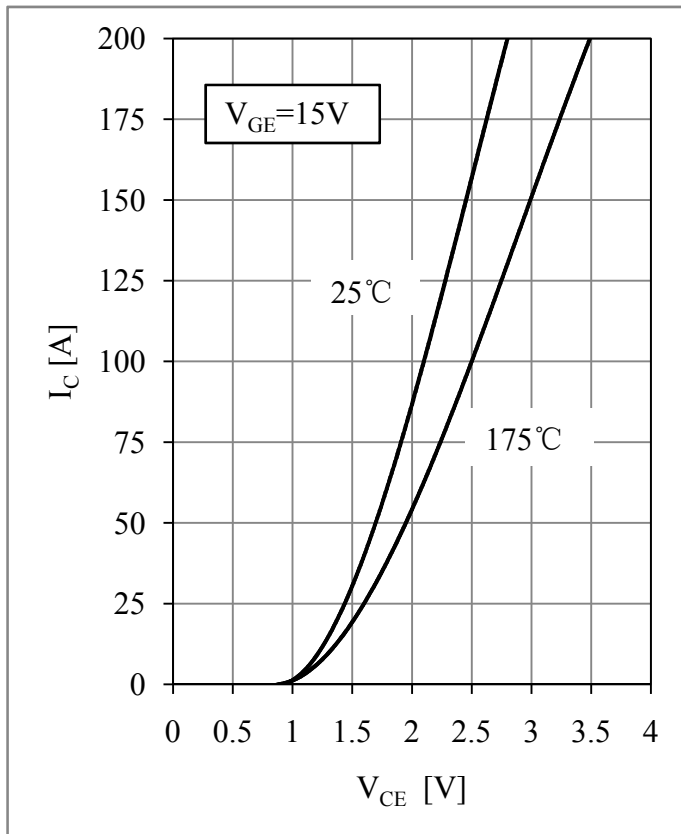


Fig 1. IGBT Output Characteristics

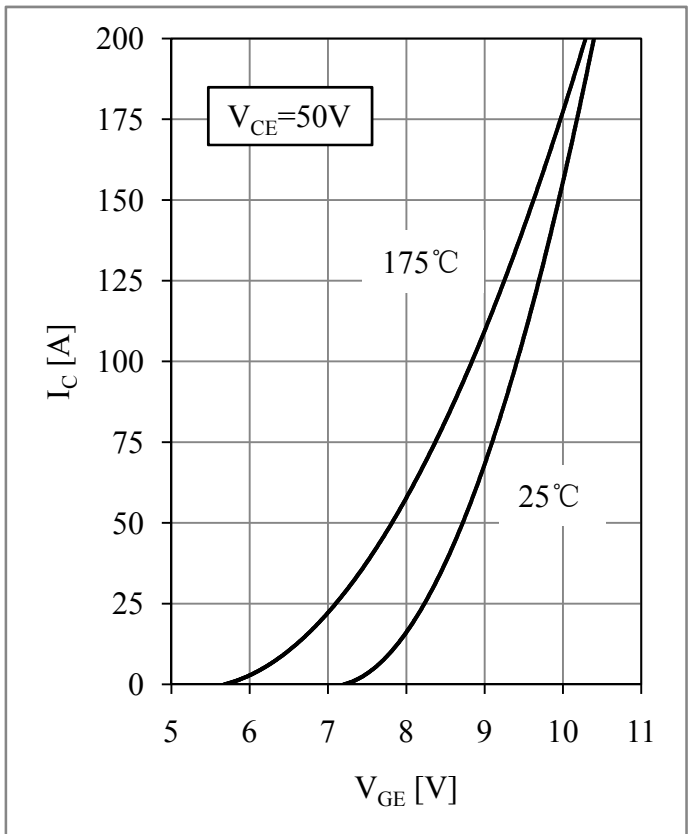
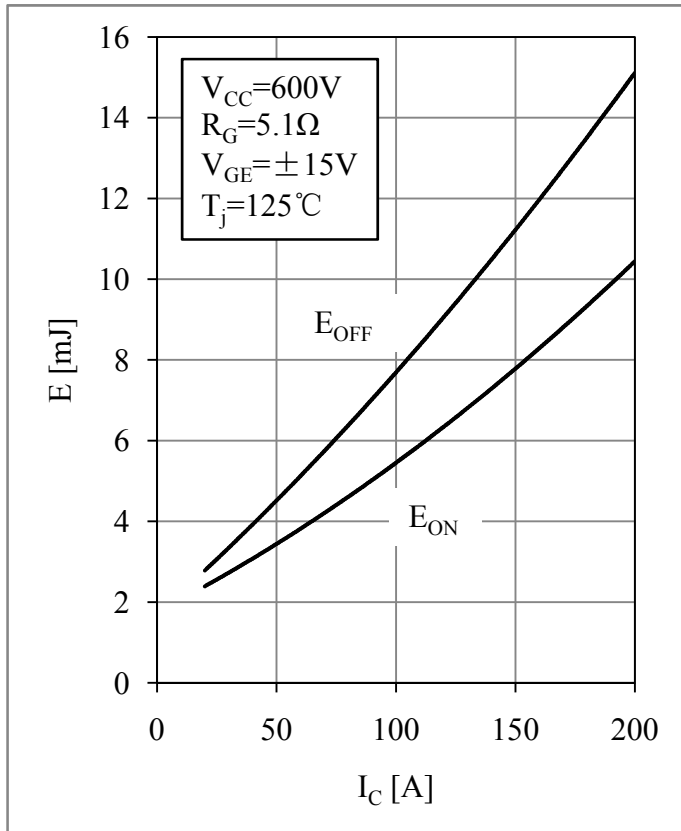
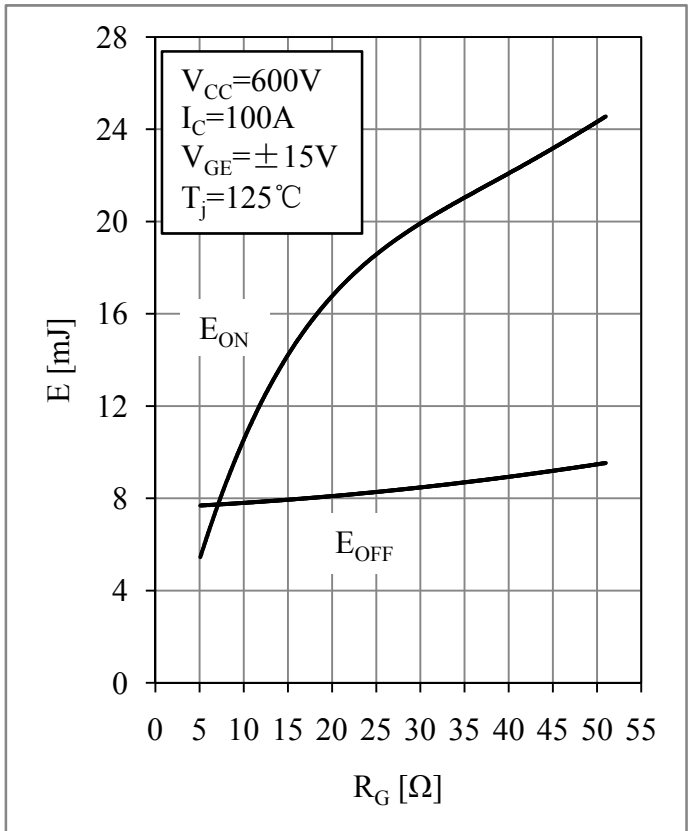


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs. I_C Fig 4. IGBT Switching Loss vs. R_G

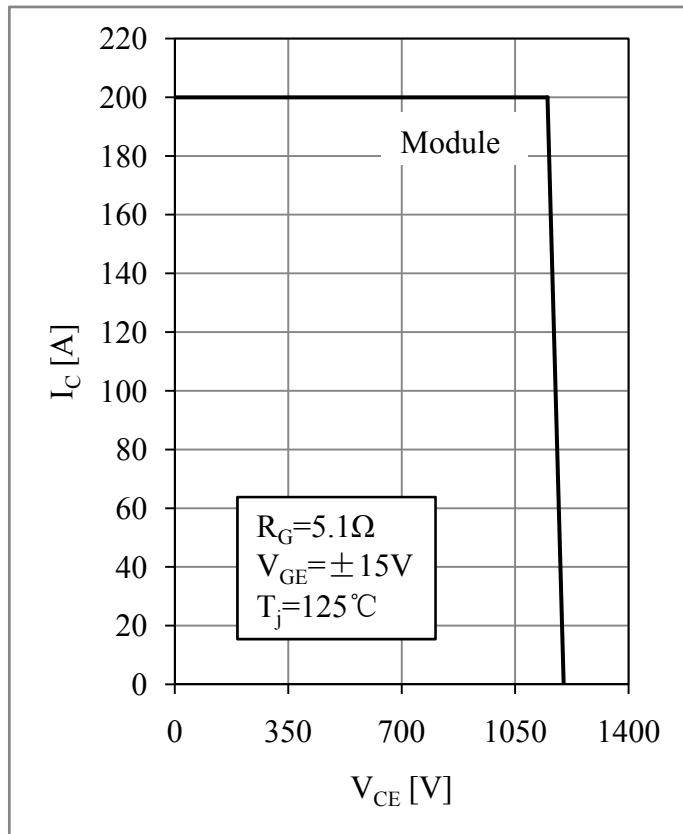


Fig 5. RBSOA

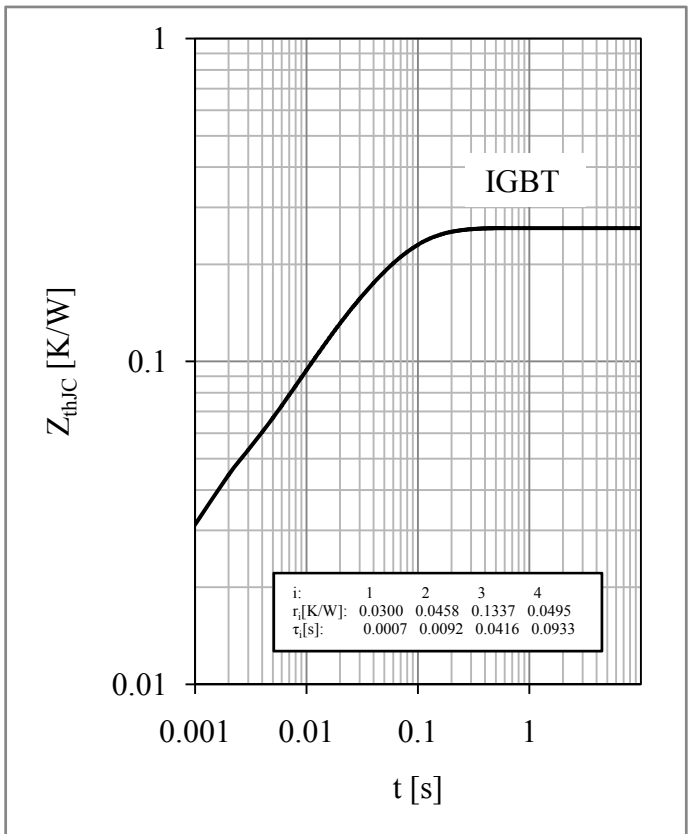


Fig 6. IGBT Transient Thermal Impedance

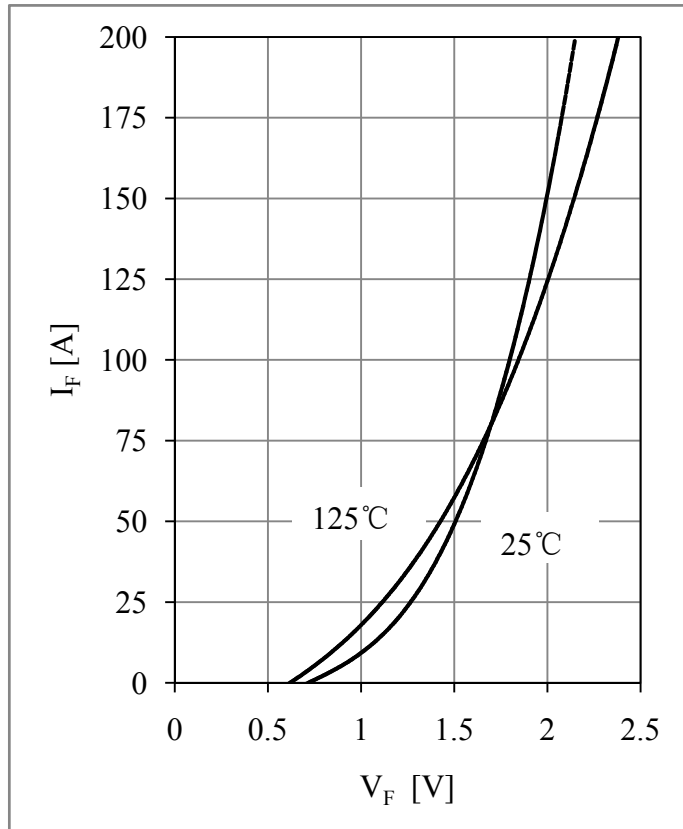
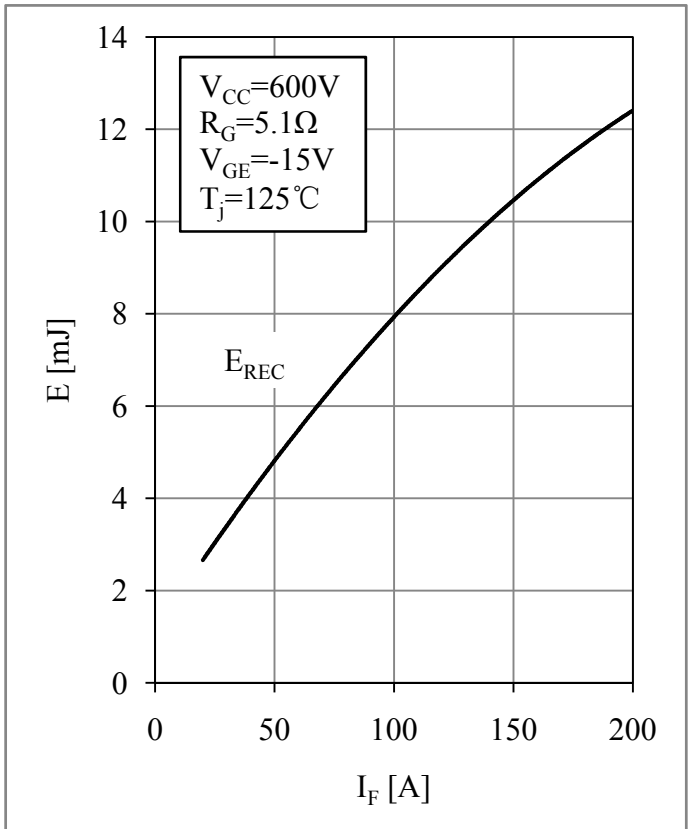


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs. I_F

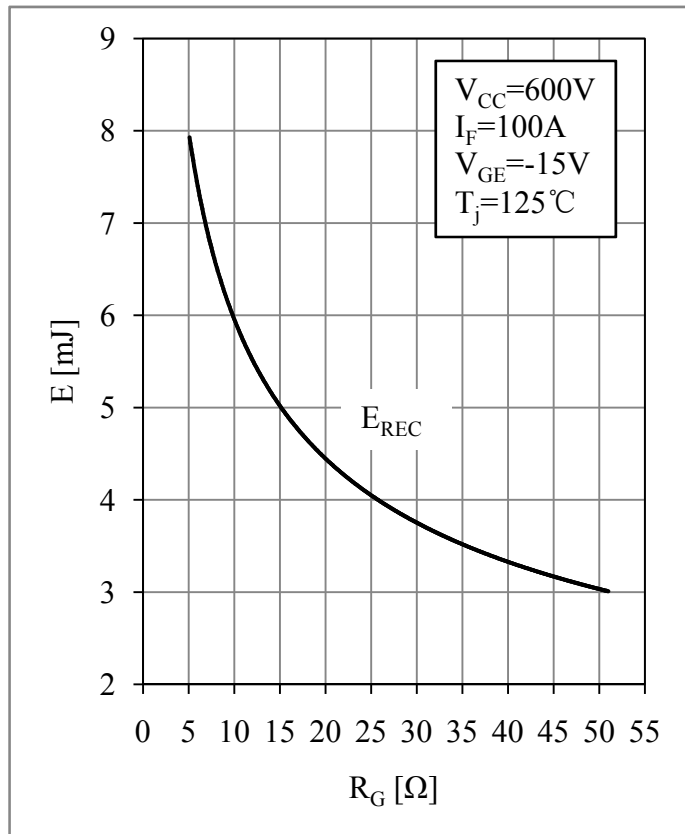
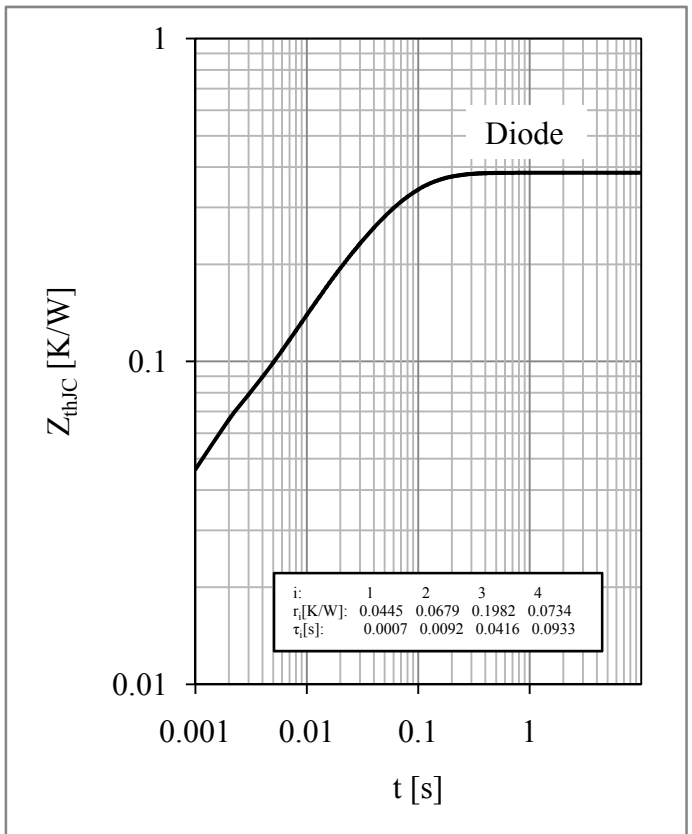
Fig 9. Diode Switching Loss vs. R_G 

Fig 10. Diode Transient Thermal Impedance

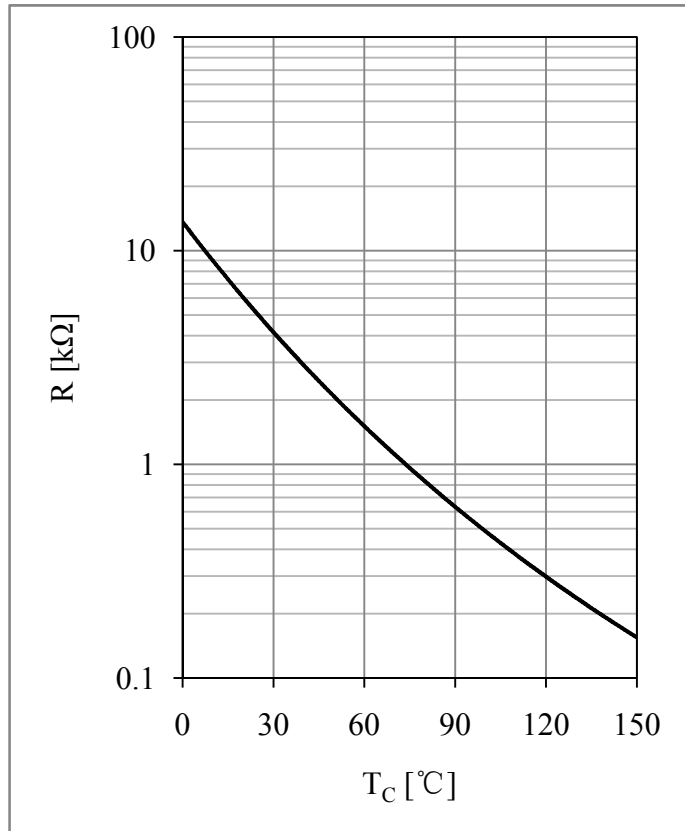
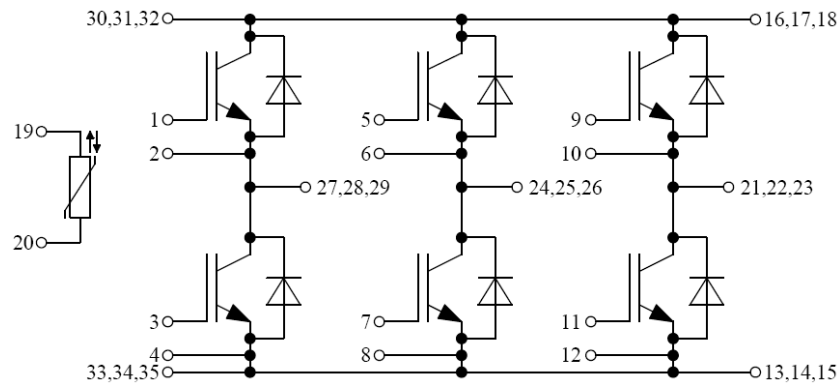


Fig 11. NTC-Temperature Characteristic

Equivalent Circuit Schematic



Package Dimensions

Dimensions in Millimeters

